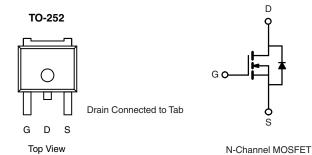


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.014			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.017			
I _D (A)	40			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- \bullet 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD40N06-14L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	T _C = 25 °C ^a	1	40	
	T _C = 125 °C	- I _D	29	
Continuous Source Current (Diode Conduction) ^a		Is	40	А
Pulsed Drain Current ^b		I _{DM}	160	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	32	
Single Pulse Avalanche Energy	L = U. I IIII	E _{AS}	51	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	Pn	75	W
	T _C = 125 °C	r _D	25	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	60	°C/W
Junction-to-Case (Drain)		R_{thJC}	2	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	1	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	1	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.011	0.014	Ω	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.024		
Dialii-Source Oil-State nesistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.029		
		V _{GS} = 4.5 V	I _D = 20 A, T _J = 25 °C	-	0.014	0.017		
Forward Transconductancea	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	52	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			ı	1685	2105		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 V$ $V_{DS} = 25 V, f = 1 MHz$	ı	305	385	pF	
Reverse Transfer Capacitance	C _{rss}			1	180	225		
Total Gate Charge ^c	Qg			-	34	51		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 40 \text{ A}$	-	6	9	nC	
Gate-Drain Charge ^c	Q_{gd}			-	8.5	13		
Gate Resistance	R_{g}	f = 1 MHz		1.20	2.46	3.70	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.75 Ω I_D \cong 40 A, V_{GEN} = 10 V, R_g = 1 Ω		-	13	20	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	22	33		
Fall Time ^c	t _f			-	9	14		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	160	Α	
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0		-	0.85	1.2	V	

Notes

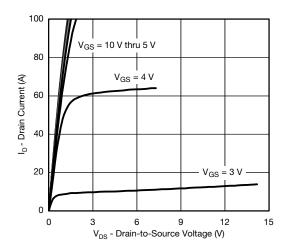
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

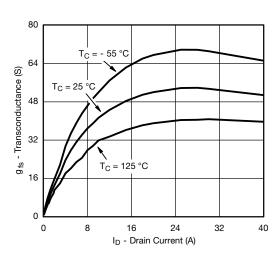


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

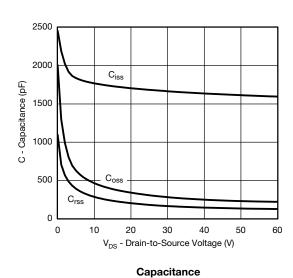
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

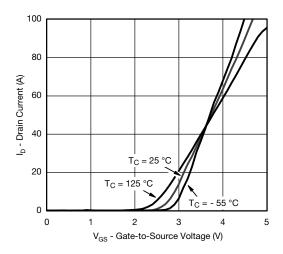


Output Characteristics

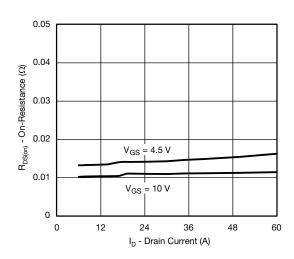


Transconductance

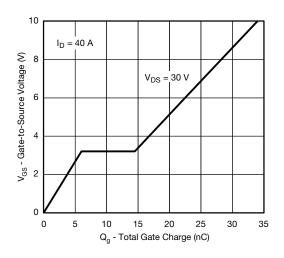




Transfer Characteristics



On-Resistance vs. Drain Current

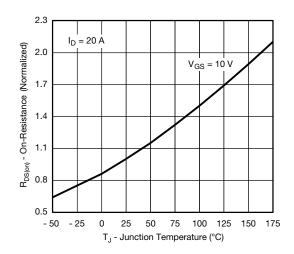


Gate Charge

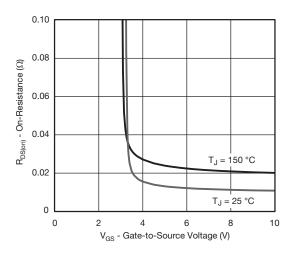


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

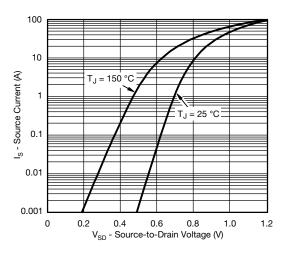
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



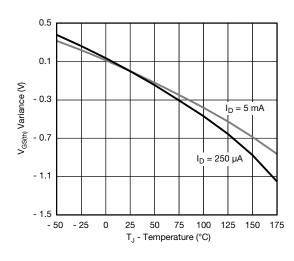
On-Resistance vs. Junction Temperature



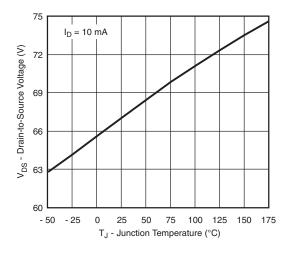
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



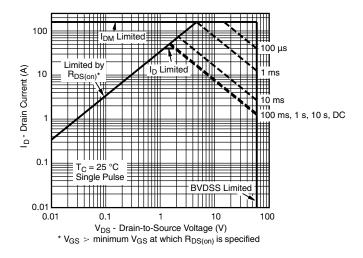
Threshold Voltage



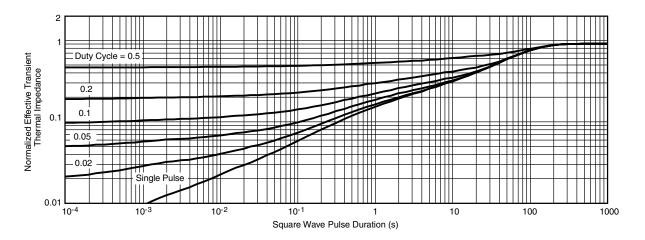
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



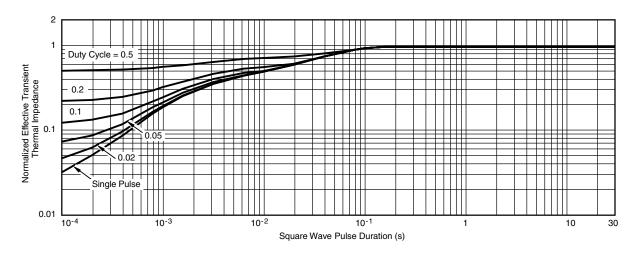
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

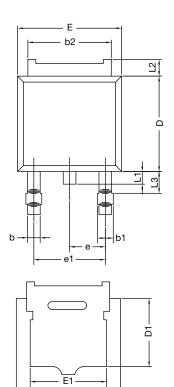
Note

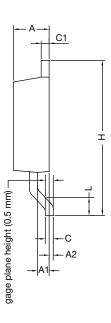
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



Automotive N-Channel 60 V (D-S) 175 °C MOSFET

TO-252AA CASE OUTLINE





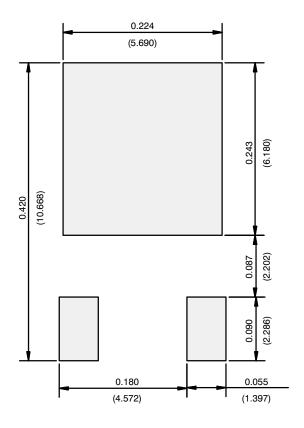
	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57	BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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Automotive N-Channel 60 V (D-S) 175 °C MOSFET

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